

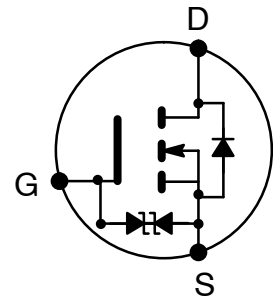


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NTE2925 MOSFET N-Ch, Enhancement Mode High Speed Switch TO-220 Full Pack Type Package

Features:

- Low Drain-Source ON Resistance: $R_{DS(ON)} = 1.35\Omega$ Typ.
- High Forward Transfer Admittance: $|Y_{fs}| = 5.0S$ Typ.
- Low Leakage Current: $I_{DSS} = 100\mu A$ Max. ($V_{DS} = 640V$)
- Enhancement-Model: $V_{th} = 2.0V$ to $4.0V$ ($V_{DS} = 10V, I_D = 1mA$)



Absolute Maximum Ratings: ($T_A = +25^\circ C$, Note 1 unless otherwise specified)

Drain-Source Voltage, V_{DSS}	800V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$), V_{DGR}	800V
Gate-Source Voltage, V_{GSS}	± 30
Drain Current (Note 2), I_D	
DC	6.A
Pulsed	18A
Drain Power Dissipation ($T_C = +25^\circ C$), P_D	45W
Single Pulse Avalanche Energy (Note 3), E_{AS}	317mJ
Avalanche Current, I_{AR}	6A
Repetitive Avalanche Energy (Note 4), E_{AR}	15mJ
Channel Temperature, T_{ch}	$+150^\circ C$
Storage Temperature Range, T_{stg}	-55° to $+150^\circ C$
Thermal Resistance, Channel-to-Case, R_{thCH-C}	$2.78^\circ C/W$
Thermal Resistance, Channel-to-Ambient, R_{thCH-A}	$62.5^\circ C/W$

Note 1. Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc. may cause this device to decrease in reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the Absolute Maximum Ratings. This transistor is an electrostatic sensitive device. Please handle with caution.

Note 2. Make sure that the device channel temperature is below $+150^\circ C$.

Note 3. $V_{DD} = 90V$, $T_{ch} = +25^\circ C$ (Initial), $L = 14.5mH$, $R_G = 25\Omega$, $I_{AR} = 6A$

Note 4. Repetitive rating; pulse width limited by maximum channel temperature.



Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 25\text{V}, V_{DS} = 0\text{V}$	-	-	± 10	μA
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	$V_{DS} = 0\text{V}, I_G = \pm 10\mu\text{A}$	± 30	-	-	V
Drain Cut-Off Current	I_{DSS}	$V_{DS} = 640\text{V}, V_{GS} = 0\text{V}$	-	-	100	μA
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{V}, I_D = 10\text{mA}$	800	-	-	V
Gate Threshold Voltage	V_{th}	$V_{DS} = 10\text{V}, I_D = 1\text{mA}$	2.0	-	4.0	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 3\text{A}$	-	1.35	1.7	Ω
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 20\text{V}, I_D = 3\text{A}$	2.5	5.0	-	S
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$	-	1400	-	pF
Output Capacitance	C_{oss}		-	130	-	pF
Reverse Transfer Capacitance	C_{rss}		-	30	-	pF
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 400\text{V}, I_D = 3\text{A}, R_L = 133\Omega,$ Note 5	-	80	-	ns
Rise Time	t_r		-	25	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	220	-	ns
Fall Time	t_f		-	65	-	ns
Total Gate Charge	Q_g	$I_D = 6\text{A}, V_{DS} = 400\text{V}, V_{GS} = 10\text{V}$	-	-	45	nC
Gate-to-Source Charge	Q_{gs}		-	-	25	nC
Gate-to-Drain ("Miller") Charge	Q_{gd}		-	-	20	nC

Note 5. Duty Cycle $\leq 1\%$, $t_w = 10\mu\text{s}$.

Source-Drain Ratings and Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Continuous Drain Reverse Current	I_{DR}	Note 2	-	-	6	A
Pulsed Drain Reverse Current	I_{DRP}	Note 2	-	-	18	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 6\text{A}, V_{GS} = 0\text{V}$	-	-	-1.7	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 6\text{A}, V_{GS} = 0\text{V},$ $di_{DR}/dt = 100\text{A}/\mu\text{s}$	-	1100	-	ns
Reverse Recovery Charge	Q_{rr}		-	10	-	μC

Note 2. Make sure that the device channel temperature is below $+150^\circ\text{C}$.

